

## NAPC/PHILIPS SEMICOND

FOR DETAILED INFORMATION SEE THE LATEST ISSUE OF HANDBOOK SC10a OR DATASHEET

## SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a microminiature plastic envelope, intended for applications in thick and thin-film circuits such as self-oscillating mixer in u.h.f. tuners in conjunction with bipolar transistors or with MOS fets.

## QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	35 V
Collector current (d.c.)	$-I_C$	max.	30 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	$P_{tot}$	max.	250 mW
Junction temperature	$T_j$	max.	150 $^{\circ}\text{C}$
Transition frequency at $f = 100\text{ MHz}$ $I_E = 3\text{ mA}; -V_{CB} = 10\text{ V}$	$f_T$	typ.	900 MHz

## MECHANICAL DATA

Dimensions in mm

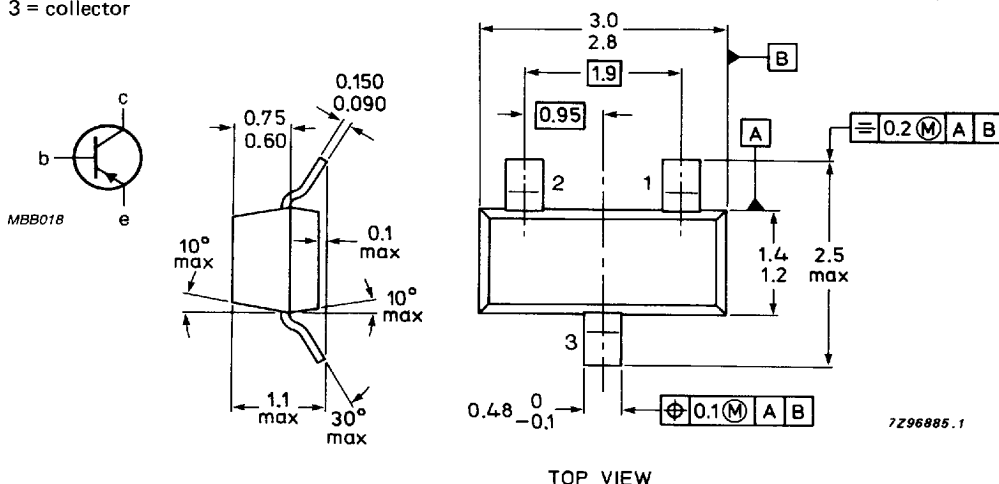
Fig. 1 SOT-23

## Pinning:

- 1 = base
- 2 = emitter
- 3 = collector

Marking code

BF569 = LHp

See also *Soldering recommendations*.